

ABSTRACT OF THE DISCLOSURE

A semiconductor device including a drain layer having a first conductivity type, a drift layer having the first conductivity type, which is formed on the drain layer and has an impurity concentration lower than that in the drain layer, and a RESURF layer having a second conductivity type and formed to extend from a surface of the drift layer into the drain layer, the RESURF layer forming a superjunction structure together with the drift layer and forming a depletion layer in the drift layer.